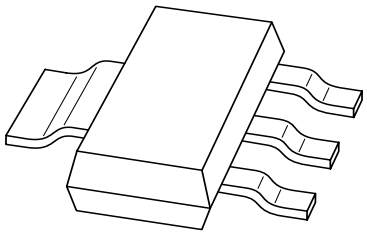
DATA SHEET



PZTA44
NPN high-voltage transistor

Product data sheet
Supersedes data of 1998 Nov 26

1999 May 21

NPN high-voltage transistor PZTA44

FEATURES

- Low current (max. 300 mA)
- High voltage (max. 400 V).

APPLICATIONS

- Telecommunication.

DESCRIPTION

NPN high-voltage transistor in a SOT223 plastic package.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter

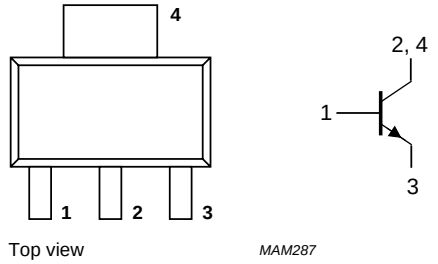


Fig.1 Simplified outline (SOT223) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	500	V
V_{CEO}	collector-emitter voltage	open base	–	400	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	300	mA
I_{CM}	peak collector current		–	300	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	1.35	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	91	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point		10	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

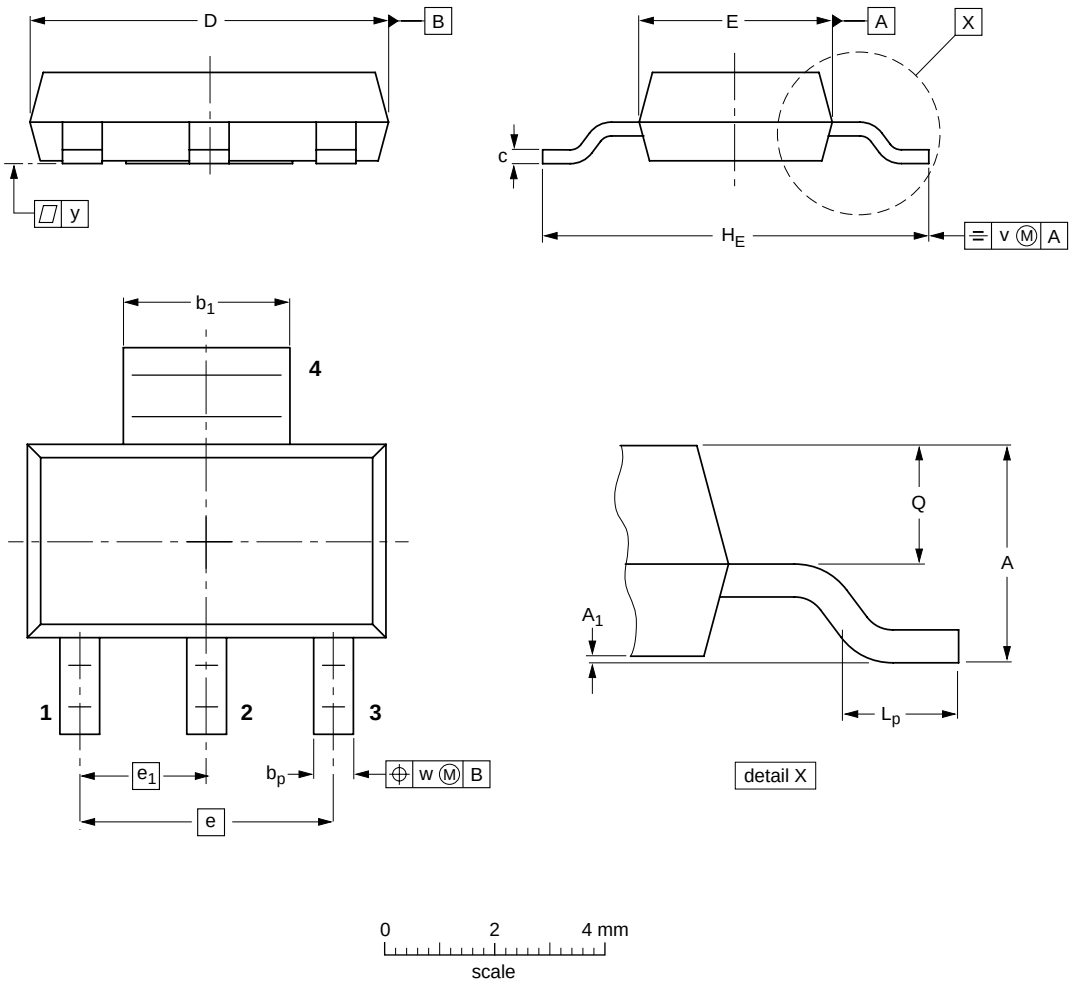
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 400 V	–	100	nA
		I_E = 0; V_{CB} = 400 V; T_j = 150 °C	–	10	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 4 V	–	100	nA
h_{FE}	DC current gain	V_{CE} = 10 V			
		I_C = 1 mA	40	–	
		I_C = 10 mA	50	200	
		I_C = 50 mA; note 1	45	–	
		I_C = 100 mA; note 1	40	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 1 mA; I_B = 0.1 mA	–	400	mV
		I_C = 10 mA; I_B = 1 mA	–	500	mV
		I_C = 50 mA; I_B = 5 mA; note 1	–	750	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 1 mA; note 1	–	850	mV
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = 20 V; f = 1 MHz	–	7	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = 500 mV; f = 1 MHz	–	180	pF
f_T	transition frequency	I_C = 10 mA; V_{CE} = 10 V; f = 100 MHz	20	–	MHz

Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			~~97-02-28~~ 99-09-13

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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